Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	751	(semiconductor or chip) and RESURF	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 12:47
S2	622	S1 and (breakdown)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 13:19
S3	333	S2 and impurity	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 13:19
S4	183	S3 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 16:20
S5	78	S4 and @pd < "20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 13:29
S6	43	S5 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/22 13:30
S9	751	(semiconductor or chip) and RESURF	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 13:09
S10	622	S9 and (breakdown)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:02
S11	333	S10 and impurity	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:02
S12	183	S11 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:02

S13	78	S12 and @pd < "20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:02
S14	43	S13 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:02
S15	43	S14	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:04
S16	96	S9 and (leakage adj current)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:04
S17	95	S16 not S15	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:24
S18	1	("4044373").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 11:24
S19	491	(257/499).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 11:27
S20	65	S19 and (isolation adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:28
S21	39	S20 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:28
S22	21	S21 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:30

S23	374	S19 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:31
S24	353	S23 not S22	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:31
S25	132	S24 and current	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:31
S26	25	S25 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:36
S27	26	S25 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:36
S28	21	S27 not S26	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:38
S29	46	S28 or S27 or S26	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:39
S30	89	S28 or S27 or S26 or S14	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:39
S31	160	RESURF and (breakdown adj voltage) and buried and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 11:40
S32	159	S31 and (chip or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 11:41

S33	145	S32 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 16:20
S34	66	S33 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:40
S35	1	("6084263").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:41
S36	1	("6707104").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:46
S37	1	("6100549").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:47
S38	1	("6362064").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:48
S39	1	("6867456").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:49
S40	1	("5640034").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:50
S41	1	("5569949").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:51
S42	1	("20020113286").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:57

S43	1	("20020113286").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 12:57
S44	4	S9 and (trench near current)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 13:10
S45	81	S9 and (trench with current)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 13:10
S46	77	S45 not S44	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 13:20
S47	1	("20020100935").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 13:27
S48	1	("20030047776").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 13:30
S49	1	("5637898").PN.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/09/23 13:42
S50	327	(semicondutor or chip)and (trench with isolation) and (breakdown adj voltage) and (leakage adj current)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 13:47
S51	159	(semicondutor or chip)and (trench with isolation) and (breakdown adj voltage) and (leakage adj current)and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:06
S52	92	(trench adj capacitor) and (breakdown adj voltage) and (leakage adj current) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:06

S53	57	(trench adj capacitor) and (breakdown adj voltage) and (leakage adj current) and trench and (chip or semiconductor) and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:24
S54	253	(trench adj isolation) and (breakdown adj voltage) and (leakage adj current) and trench and (chip or semiconductor) and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:30
S55	253	S54 notL49	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:24
S56	226	S54 not S53	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:25
S57	226	S54 not (S53 and S52)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:25
S58	1	(trench near conductor) and (breakdown adj voltage) and (leakage adj current) and trench and (chip or semiconductor) and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:31
S59	94	(trench near (metal or silicon or conduct$4)) and (breakdown adj voltage) and (leakage adj current) and trench and (chip or semiconductor) and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 14:32
S60	102	hvic and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 16:21
S61	124	hvic and (semiconductor or chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 17:02
S62	2294	(chip or semiconductor) and gate and ((trench near substrate) or (trench with substrate)) and (leakage near current) and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 17:04

S63	2293	S62 not S61	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 17:04
S64	65	S63 and (field near plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/30 17:04
S65	618	(257/339).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:14
S66	422	(257/343).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 08:20
S69	86	(257/489).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:42
S70	110	(257/490).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:53
S71	185	(257/491).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S72	195	(257/492).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S73	182	(257/493).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S74	202	(257/494).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12

S75	232	(257/495).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S76	1197	(257/506).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S77	244	(257/509).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:12
S78	844	(257/510).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S79	309	(257/513).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S80	152	(257/514).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S81	339	(257/544).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S82	378	(257/500).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S83	412	(257/508).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/03 16:13
S85	502	S65 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/03 16:15

S86	263	(257/337).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:05
S87	254	(257/488).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:06
S88	218	S87 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 09:41
S89	86	(257/489).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:42
S90	70	S89 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 09:52
S91	110	(257/490).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 09:53
S92	89	S91 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 10:15

S93	62	(US-20020027259-$ or US-20020030226-$ or US-20020043699-$ or US-20020102808-$ or US-20020113286-$ or US-20020179974-$ or US-20020195659-$ or US-20030168710-$ or US-20030214009-$ or US-20040124464-$ or US-20050056906-$ or US-20050144539-$ or US-20050146823-$ or US-20050169026-$ or US-20050179089-$ or US-20050194656-$ or US-20020017683-$ or US-20010009287-$).did. or (US-4661838-$ or US-4890146-$ or US-4933739-$ or US-5021852-$ or US-5485027-$ or US-5514608-$ or US-5624858-$ or US-5637898-$ or US-5793065-$ or US-5912495-$ or US-5925900-$ or US-5986301-$ or US-6037634-$ or US-6124628-$ or US-6198130-$ or US-6246101-$ or US-6252258-$ or US-6323509-$ or US-6323539-$ or US-6507085-$ or US-6586780-$ or US-6603176-$ or US-6707104-$ or US-6750524-$ or US-6864550-$ or US-6927455-$). did. or (US-6552389-$ or US-6501129-$ or US-6445019-$ or US-6194761-$ or US-5742087-$ or US-5525821-$ or US-5191396-$ or US-4707720-$ or US-6924531-$ or US-6806533-$ or US-5598018-$ or US-4949142-$ or US-6064074-$ or US-5914523-$ or US-5898199-$ or US-4868921-$ or US-5113237-$ or US-5233215-$).did.	US-PGPUB; USPAT	OR	OFF	2005/10/04 10:28
S94	185	(257/491).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 10:28
S95	140	S94 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04

S96	755	(semiconductor or chip) and RESURF	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S97	625	S96 and (breakdown)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S98	335	S97 and impurity	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S99	183	S98 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S100	78	S99 and @pd < "20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S101	43	S100 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S102	755	(semiconductor or chip) and RESURF	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S103	625	S102 and (breakdown)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S104	335	S103 and impurity	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S105	183	S104 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04

S106	78	S105 and @pd < "20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S107	43	S106 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S108	492	(257/499).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S109	65	S108 and (isolation adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S110	39	S109 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S111	21	S110 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S112	374	S108 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S113	353	S112 not S111	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S114	132	S113 and current	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S115	25	S114 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04

S11 6	26	S114 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S11 7	21	S116 not S115	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S11 8	46	S117 or S116 or S115	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S11 9	89	S117 or S116 or S115 or S107	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S12 0	161	RESURF and (breakdown adj voltage) and buried and isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S12 1	160	S120 and (chip or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S12 2	146	S121 not S119	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S12 3	66	S122 and @pd<"20030520"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 13:04
S12 4	86	(257/489).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S12 5	70	S124 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04

S126	110	(257/490).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S127	89	S126 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S128	185	(257/491).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S129	140	S128 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:04
S130	7757	(S101 or "S125" or S111 or "S96" or S125 or S127 or S129 or S123 or S119 or S118)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:06
S131	3273	(257/506,509,510,513,514,544,500, 508).CCLS.	US-PGPUB; USPAT; USOCR; JPO; IBM_TDB	OR	OFF	2005/10/04 13:07
S133	2566	S131 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:07
S134	2517	S133 not S130	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:19
S135	781	S134 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:19
S136	331	S135 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 13:20

S13 7	59	S135 and trench and plate	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/10/04 14:10
S13 8	755	(semiconductor or chip)and RESURF	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 14:11
S13 9	373	S138 and buried	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 14:11
S14 0	173	S139 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 14:11
S14 1	69	S140 and @pd<"20030503"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/04 14:11